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Kind regards,

Team Nexperia

HEF4069UB-Q100

Hex inverter

Rev. 2 — 9 September 2014

Product data sheet

1. General description

The HEF4069UB-Q100 is a general-purpose hex inverter. Each inverter has a single stage.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - \bullet MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Complies with JEDEC standard JESD 13-B

3. Applications

Oscillator

4. Ordering information

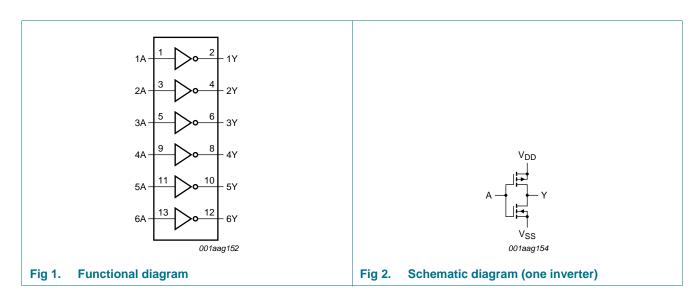
Table 1. Ordering information

All types operate from -40 °C to +125 °C.

Type number	Package	ackage							
	Name	Description	Version						
HEF4069UBT-Q100	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1						
HEF4069UBTT-Q100	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1						

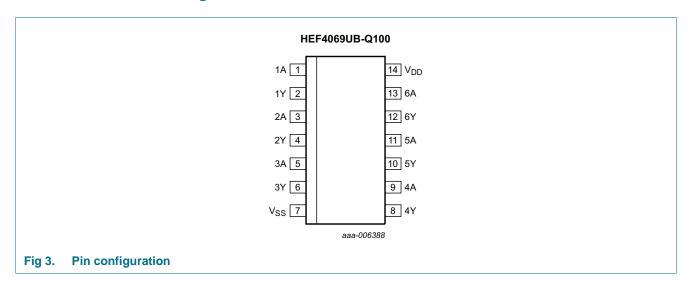


5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 6A	1, 3, 5, 9, 11, 13	input
1Y to 6Y	2, 4, 6, 8, 10, 12	output
V_{SS}	7	ground (0 V)
V_{DD}	14	supply voltage

HEF4069UB_Q100

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7. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
V_{DD}	supply voltage			-0.5	+18	V	
I _{IK}	input clamping current	nt $V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$		-	±10	mA	
VI	input voltage			-0.5	V _{DD} + 0.5	V	
I _{OK}	output clamping current	utput clamping current $V_O < -0.5 \text{ V or } V_O > V_{DD} + 0.5 \text{ V}$		-	±10	mA	
I _{I/O}	input/output current			-	±10	mA	
I _{DD}	supply current			-	50	mA	
T _{stg}	storage temperature			-65	+150	°C	
T _{amb}	ambient temperature			-40	+125	°C	
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$					
		SO14	<u>[1]</u>	-	500	mW	
		TSSOP14	[2]	-	500	mW	
Р	power dissipation	per output		-	100	mW	

^[1] For SO14 packages: above T_{amb} = 70 °C, P_{tot} derates linearly with 8 mW/K.

8. Recommended operating conditions

Table 4. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	supply voltage		3	-	15	V
VI	input voltage		0	-	V_{DD}	V
T _{amb}	ambient temperature	in free air	-40	-	+125	°C

^[2] For TSSOP14 packages: above T_{amb} = 60 °C, P_{tot} derates linearly with 5.5 mW/K.

9. Static characteristics

Table 5. Static characteristics

 $V_{SS} = 0$ V; $V_I = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T _{amb} =	–40 °C	T _{amb} =	+25 °C	T _{amb} =	+85 °C	T _{amb} = +125 °C		Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V _{IH}	HIGH-level	$ I_{O} < 1 \mu A$	5 V	4	-	4	-	4	-	4	-	V
	input voltage		10 V	8	-	8	-	8	-	8	-	V
			15 V	12.5	-	12.5	-	12.5	-	12.5	-	V
V _{IL}	LOW-level	$ I_{O} < 1 \mu A$	5 V	-	1	-	1	-	1	-	1	V
	input voltage		10 V	-	2	-	2	-	2	-	2	V
			15 V	-	2.5	-	2.5	-	2.5	-	2.5	V
V _{OH}	HIGH-level	$ I_{O} < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V
	output voltage		10 V	9.95	-	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V
V _{OL}	LOW-level	$ I_{O} < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
	output voltage		10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I _{OH}	HIGH-level	$V_0 = 2.5 \text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	-	-1.1	mA
	output current	V _O = 4.6 V	5 V	-	-0.64	-	-0.5	-	-0.36	-	-0.36	mA
		$V_0 = 9.5 \text{ V}$	10 V	-	-1.6	-	-1.3	-	-0.9	-	-0.9	mA
		V _O = 13.5 V	15 V	-	-4.2	-	-3.4	-	-2.4	-	-2.4	mA
I _{OL}	LOW-level	$V_0 = 0.4 \text{ V}$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mA
	output current	$V_0 = 0.5 \text{ V}$	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mA
		V _O = 1.5 V	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mA
I _I	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μА
I _{DD}	supply current	all valid input	5 V	-	0.25	-	0.25	-	7.5	-	7.5	μА
		combinations;	10 V	-	0.5	-	0.5	-	15.0	-	15.0	μА
		$I_O = 0 A$	15 V	-	1.0	-	1.0	-	30.0	-	30.0	μА
C _I	input capacitance	digital inputs		-	-	-	7.5	-	-	-	-	pF

10. Dynamic characteristics

Table 6. Dynamic characteristics

 $T_{amb} = 25$ °C; for waveforms see <u>Figure 4</u>; for test circuit see <u>Figure 5</u>.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula[1]	Min	Тур	Max	Unit
t _{PHL}	HIGH to LOW	nA to nY	5 V	18 ns + (0.55 ns/pF)C _L	-	45	90	ns
	propagation delay		10 V	9 ns + (0.23 ns/pF)C _L	-	20	40	ns
			15 V	7 ns + (0.16 ns/pF)C _L	-	15	25	ns
t _{PLH}	LOW to HIGH	nA to nY	5 V	13 ns + (0.55 ns/pF)C _L	-	40	80	ns
	propagation delay		10 V	9 ns + (0.23 ns/pF)C _L	-	20	40	ns
		15 V	7 ns + (0.16 ns/pF)C _L	-	15	30	ns	
t _{THL}	HIGH to LOW output	output nY	5 V	10 ns + (1.00 ns/pF)C _L	-	60	120	ns
	transition time		10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns
t _{TLH}	LOW to HIGH output	output nY	5 V	10 ns + (1.00 ns/pF)C _L	-	60	120	ns
	transition time		10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns

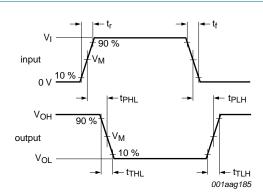
^[1] The typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C_L in pF).

Table 7. Dynamic power dissipation

 $V_{SS} = 0 \ V; \ t_f = t_f \le 20 \ ns; \ T_{amb} = 25 \ ^{\circ}C.$

Symbol	Parameter	V_{DD}	Typical formula	Where
P_D	dynamic power dissipation	5 V	$P_D = 600 \times f_i + \Sigma (f_0 \times C_L) \times V_{DD}^2 (\mu W)$	f_i = input frequency in MHz;
		10 V	$P_D = 4000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2 (\mu W)$	f _o = output frequency in MHz;
		15 V	$P_D = 22000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2 (\mu W)$	C_L = output load capacitance in pF;
				$\Sigma(f_0 \times C_L)$ = sum of the outputs;
				V _{DD} = supply voltage in V.

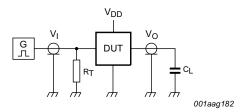
11. Waveforms



Measurement points: $V_M = 0.5V_{DD}$.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 4. Propagation delay and transition times



Definitions for test circuit:

C_L = load capacitance including jig and probe capacitance;

 R_T = termination resistance should be equal to the output impedance Z_0 of the pulse generator;

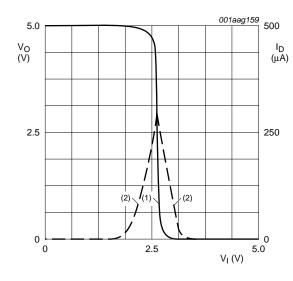
For test data, refer to Table 8.

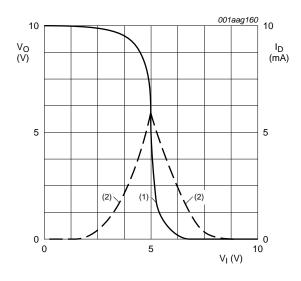
Fig 5. Test circuit for measuring switching times

Table 8. Test data

Supply voltage	Input	Load	
V_{DD}	V _I	t _r , t _f	C _L
5 V to 15 V	V_{SS} or V_{DD}	≤ 20 ns	50 pF

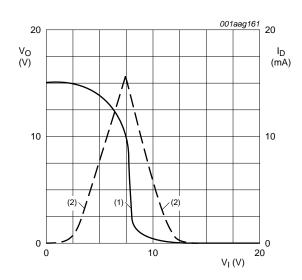
11.1 Transfer characteristics





a.
$$V_{DD} = 5 \text{ V}$$
; $I_{O} = 0 \text{ A}$





- c. $V_{DD} = 15 \text{ V}$; $I_{O} = 0 \text{ A}$
- (1) $V_O = \text{output voltage}$.
- (2) $I_D = drain current$.

Fig 6. Typical transfer characteristics

12. Application information

Some examples of applications for the HEF4069UB-Q100.

<u>Figure 7</u> shows an astable relaxation oscillator using two HEF4069UB-Q100 inverters and 2 BAW62 diodes. The oscillation frequency is mainly determined by R1 \times C1, provided R1 << R2 and R2 \times C2 << R1 \times C1.

The function of R2 is to minimize the influence of the forward voltage across the protection diodes on the frequency; C2 is a stray (parasitic) capacitance.

The period T_p is given by $T_p = T_1 + T_2$,

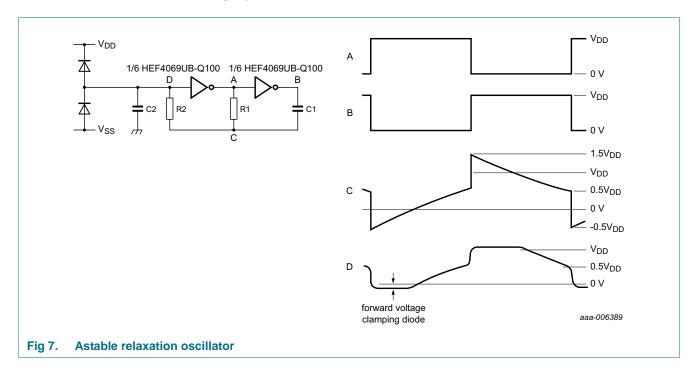
where:

$$T_1 = R1C1In \frac{V_{DD} + V_{ST}}{V_{ST}}$$

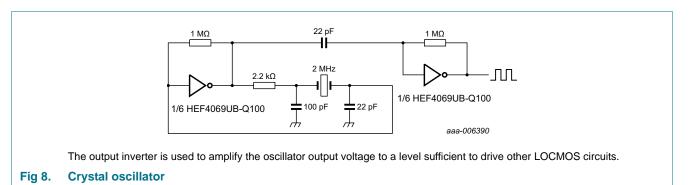
$$T_2 = RICIIn \frac{2V_{DD} - V_{ST}}{V_{DD} - V_{ST}}$$

 V_{ST} = the signal threshold level of the inverter.

The period is fairly independent of V_{DD} , V_{ST} and temperature. The duty factor, however, is influenced by V_{ST} .



<u>Figure 8</u> shows a crystal oscillator for frequencies up to 10 MHz using two HEF4069UB-Q100 inverters. The second inverter amplifies the oscillator output voltage to a level sufficient to drive other Local Oxidation CMOS (LOCMOS) circuits.



<u>Figure 9</u> and <u>Figure 10</u> show voltage gain and supply current. <u>Figure 11</u> shows the test set-up and an example of an analog amplifier using one HEF4069UB-Q100.

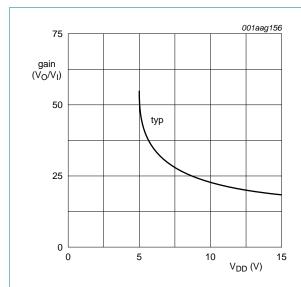


Fig 9. Typical voltage gain as a function of supply voltage

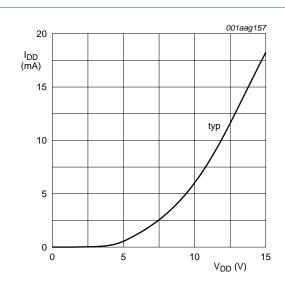
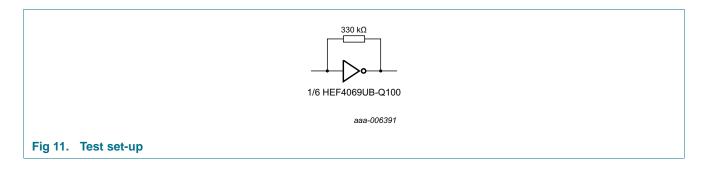


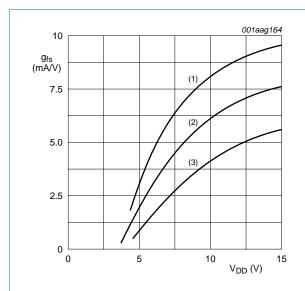
Fig 10. Typical supply current as a function of supply voltage



HEF4069UB_Q100

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Figure 12 shows typical forward transconductance and Figure 13 shows the test set-up.



- (1) Average +2 σ ; where: ' σ ' is the standard deviation.
- (2) Average.
- (3) Average -2σ ; where: ' σ ' is the standard deviation.

Fig 12. Typical forward transconductance as a function of supply voltage at $T_{amb} = 25 \, ^{\circ}\text{C}$

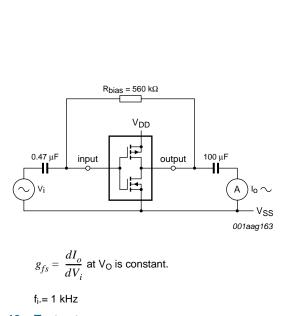
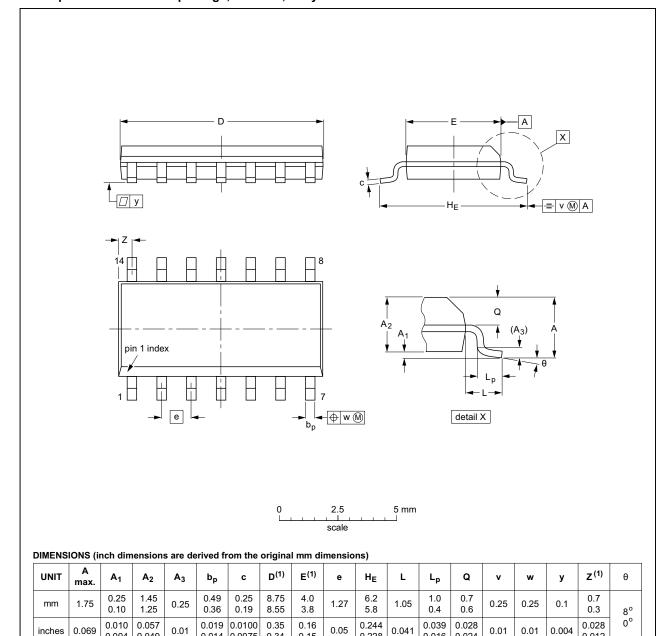


Fig 13. Test set-up

13. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

0.014 0.0075

0.34

0.15

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SOT108-1	076E06	MS-012			99-12-27 03-02-19	

0.228

0.016

0.024

Fig 14. Package outline SOT108-1 (SO14)

0.004

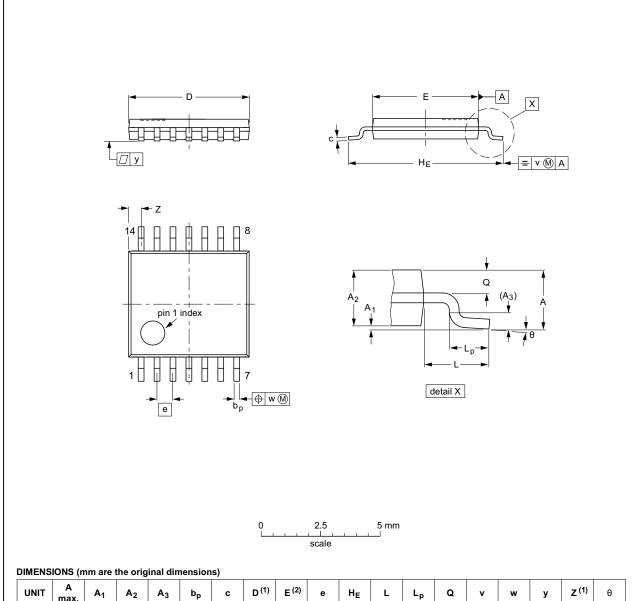
0.049

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	٧	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

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Fig 15. Package outline SOT402-1 (TSSOP14)

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14. Abbreviations

Table 9. Abbreviations

Acronym	Description
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4069UB_Q100 v.2	20140909	Product data sheet	-	HEF4069UB_Q100 v.1
Modifications:	Section 2: ESD protection: MIL-STD-833 changed to MIL-STD883			
HEF4069UB_Q100 v.1	20130228	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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